Features
- DC to 3.0 GHz
- Flanged model
- Low VSWR
- Beryllium Oxide ceramic

Applications
- High power RF transmission
- Power Dividers/Combiners

General Specifications
Substrate: Beryllium Oxide ceramic
Resistive Film: Thick Film
Tab: Silver
Cover Substrate: Al203
Mounting Flange: Cu plated with Ni
Resistance: 12.5, 25, 50 or 100 ohms
Tolerance: ±5%
Capacitance (Resistor Only): 4.1 pF
Packaging: 60 pcs./tray

Absolute Ratings
Power: 250 W
Frequency: 3.0 GHz
VSWR: 1.25 Maximum

Characteristic Curve
- Power (Watts) vs. Heat Sink Temperature (°C)

Product Dimensions

How To Order
Model
Size
Version
Substrate
Mount
F = Flange
Value
12R5 = 12.5 Ohms (Resistor Only)
250 = 25 Ohms (Resistor Only)
500 = 50 Ohms (Resistor and Termination)
101 = 100 Ohms (Resistor and Termination)
Function
L = Termination
R = Resistor

Specifications are subject to change without notice.
The device characteristics and parameters in this data sheet can and do vary in different applications and actual device performance may vary over time.
Users should verify actual device performance in their specific applications.